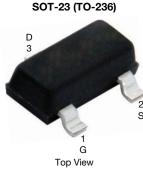
### **SQ2308CES**

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**Vishay Siliconix** 

## Automotive N-Channel 60 V (D-S) 175 °C MOSFET



#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- AEC-Q101 Qualified <sup>c</sup>
- 100 %  $R_{\rm q}$  and UIS Tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

N-Channel MOSFET



RoHS COMPLIANT HALOGEN FREE

Marking Code: 8X

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 10 V	0.150			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.164			
I <sub>D</sub> (A)	2.3			
Configuration	Single			

	-
ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2308CES (for detailed order number please see <u>www.vishay.com/doc?79771</u> )

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unless	otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	60	V
Gate-source voltage		V <sub>GS</sub>	± 20	v
Continuous drain current	T <sub>C</sub> = 25 °C	1	2.3	
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	1.3	
Continuous source current (diode conduction)		I <sub>S</sub>	2.4	А
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	9	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	7	
Single pulse avalanche energy		E <sub>AS</sub>	2.5	mJ
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	2	W
	T <sub>C</sub> = 125 °C		0.6	vv
Operating junction and storage temperature	e range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	120	°C/W	
Junction-to-foot (drain)		R <sub>thJF</sub>	80	0/10	

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. When mounted on 1" square PCB (FR-4 material)

c. Parametric verification ongoing

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<b>SPECIFICATIONS</b> ( $T_C = 25 \ ^{\circ}C$	, unless otherv	vise noted)					
PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static		·					
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	$V_{GS}$ = 0, $I_D$ = 250 $\mu$ A		-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ	1.5	2.0	2.5	v
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$=$ 0 V, V <sub>GS</sub> = $\pm$ 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	$V_{DS} = 60 V$	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = 60 V, $T_J$ = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS}$ = 60 V, $T_J$ = 175 °C	-	-	150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	10	-	-	А
Drain-source on-state resistance <sup>a</sup>		$V_{GS} = 10 V$	I <sub>D</sub> = 2.3 A	-	0.125	0.150	Ω
	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	$I_D = 2.3 \text{ A},  \text{T}_\text{J} = 125 \ ^\circ\text{C}$	-	-	0.250	
	<sup>1</sup> DS(on)	$V_{GS} = 10 V$	$I_D = 2.3 \text{ A},  \text{T}_\text{J} = 175 \ ^\circ\text{C}$	-	-	0.325	52
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 2.1 A	-	0.136	0.164	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 2.3 \text{ A}$		-	5.5	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	164	205	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 30 V$ , f = 1 MHz	-	22	28	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	14	18	
Total gate charge <sup>c</sup>	Qg			-	3.5	5.3	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 2 \text{ A}$	-	0.6	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	0.7	-	1
Gate resistance	Rg	f = 1 MHz		2.9	5.84	9	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_{\text{L}} = 15 \Omega$ $\text{I}_{\text{D}} \cong 2 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	4	6	
Rise time <sup>c</sup>	t <sub>r</sub>			-	9	13	- ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	12	17	
Fall time <sup>c</sup>	t <sub>f</sub>			-	12	18	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	9	A
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> :	= 1.6 A, V <sub>GS</sub> = 0	-	0.85	1.2	V

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

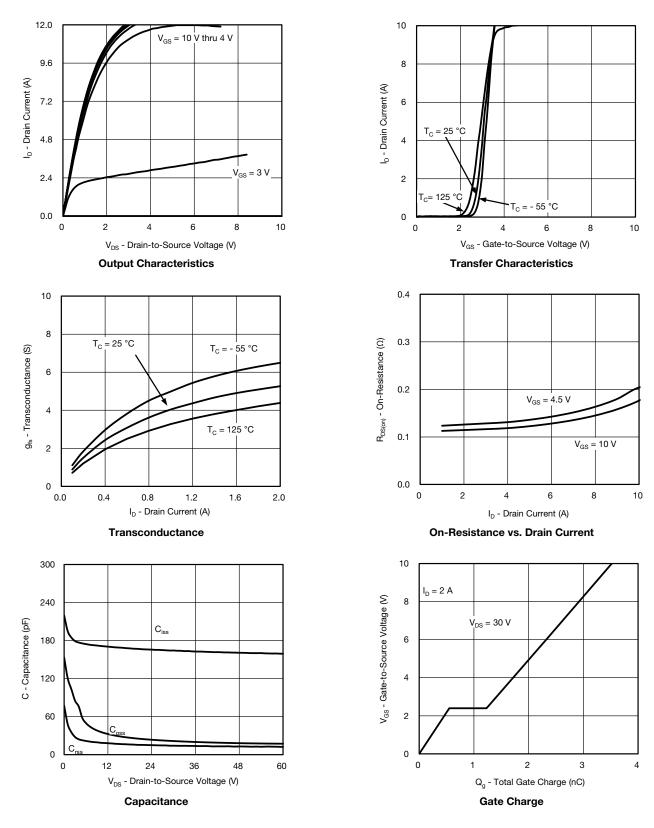
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



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 $I_D = 1 \text{ mA}$ V<sub>DS</sub> - Drain-to-Source Voltage (V) 76 72 68 64

## - 0.7 -10

T<sub>J</sub> = 25 °C 2

0.2 0.4 0.6 0.8 1.0 1.2 V<sub>SD</sub> - Source-to-Drain Voltage (V)

= 25 °C



T<sub>J</sub> = 150 °C

10

1

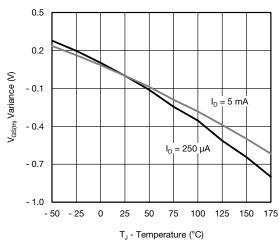
0.1

0.01

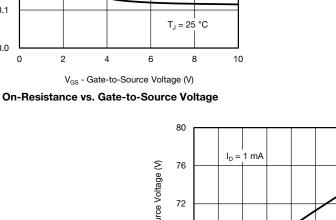
0.001

0.0

I<sub>s</sub> - Source Current (A)



**Threshold Voltage** 

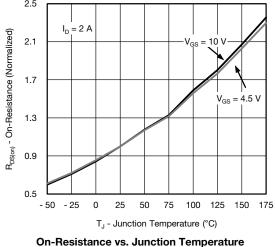


60

- 50 - 25

0 25 50 75 T<sub>J</sub> - Junction Temperature (°C) Drain Source Breakdown vs. Junction Temperature

T<sub>1</sub> = 150 °C



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0.5

0.4

0.3

0.2

0.1

0.0

0

 $R_{DS(on)}$  - On-Resistance ( $\Omega$ )

#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted) 2.5 100

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100 125

150 175

4

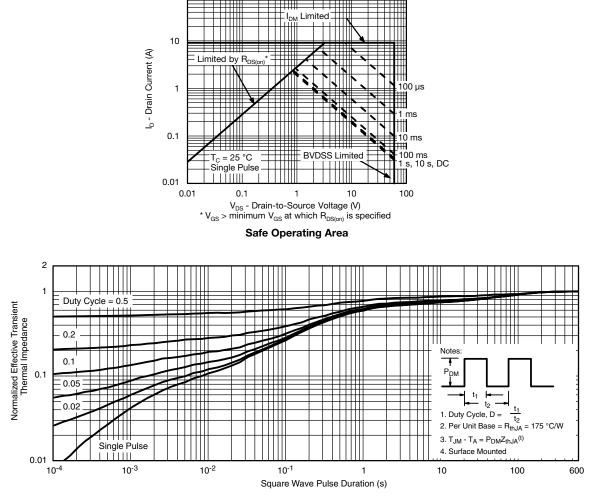


SQ2308CES

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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

100



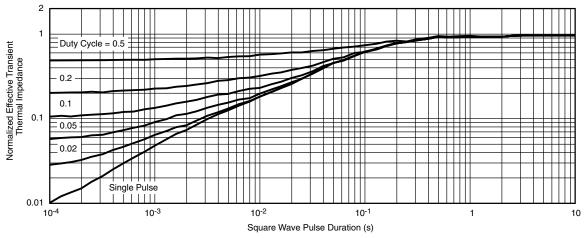
Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63877.



## Package Information

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#### SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES		
	Min	Max	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	



# Application Note 826

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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